The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-32. (Canceled)

33. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a first element-forming region and a second element-forming region using portions of the crystalline semiconductor film;

forming a gate electrode in the first element-forming region and a gate electrode in the second element-forming region over ~~a portion of~~ the crystalline semiconductor film ~~which is included in an element forming region~~; and

forming an impurity region in the first element-forming region and an impurity region in the second element-forming region in the crystalline semiconductor film using [[the]] each gate electrode as a mask,

wherein a scanning direction of the energy beam changes outside and between the first element-forming region and the second element-forming region.

34. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film;

forming a first element-forming region and a second element-forming region using portions of the crystalline semiconductor film;

forming a gate electrode in the first element-forming region and a gate electrode in the second element-forming region over ~~a portion of~~ the crystalline semiconductor film ~~which is included in an element forming region~~; and

forming an impurity region in the first element-forming region and an impurity region in the second element-forming region in the crystalline semiconductor film using [[the]] each gate electrode as a mask,

wherein the energy beam starts or ends irradiation from outside the first element-forming region and the second element-forming region ~~or ends irradiation outside the element forming region~~ and changes a scanning direction between the first element-forming region and the second element-forming region.

35. (Previously Presented) A method for manufacturing a thin film transistor according to claim 33, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

36. (Previously Presented) A method for manufacturing a thin film transistor according to claim 34, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

37. (Original) A method for manufacturing a thin film transistor according to claim 33, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

38. (Original) A method for manufacturing a thin film transistor according to claim 34, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

39. (Currently Amended) A method for manufacturing a thin film transistor according to claim 33, wherein the first element-forming region is a region where a display device or an integrated circuit is formed and the second element-forming region is a region where a display device or an integrated circuit is formed.

40. (Currently Amended) A method for manufacturing a thin film transistor according to claim 34, wherein the first element-forming region is a region where a display device or an integrated circuit is formed and the second element-forming region is a region where a display device or an integrated circuit is formed.

41. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands using the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate,

wherein the energy beam is irradiated outside and between the first circuit and the second circuit while changing a scanning direction of the energy beam.

42.-44. (Canceled)

45. (Currently Amended) A method for manufacturing ~~a semiconductor device~~ a thin film transistor according to claim 33, wherein the ~~semiconductor device~~ thin film transistor is incorporated into a semiconductor device which is further incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

46. (Currently Amended) A method for manufacturing ~~a semiconductor device~~ a thin film transistor according to claim 34, wherein the ~~semiconductor device~~ thin film transistor is incorporated into a semiconductor device which is further incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

47. (Previously Presented) A method for manufacturing a semiconductor device according to claim 41, wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

48. (Currently Amended) A method for manufacturing ~~a thin film transistor~~ a semiconductor device according to claim 41, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

49. (Currently Amended) A method for manufacturing ~~a thin film transistor~~ a semiconductor device according to claim 41, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

50. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

crystallizing the semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to the semiconductor film;

forming a plurality of semiconductor islands by using the crystallized semiconductor film;

forming a first circuit using one of the plurality of semiconductor islands over the substrate; and

forming a second circuit using another one of the plurality of semiconductor islands over the substrate,

wherein the energy beam starts or ends irradiation from outside the first circuit and the second circuit ~~or ends irradiation outside~~ and a scanning direction of the energy beam changes between the first circuit and the second circuit.

51. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a first element-forming region and a second element-forming region using portions of the crystalline semiconductor film;

forming a gate electrode in the first element-forming region and a gate electrode in the second element-forming region over ~~a portion of~~ the crystalline semiconductor film ~~which is included in an element-forming region~~; and

forming an impurity region in the first element-forming region and an impurity region in the second element-forming region in the crystalline semiconductor film using [[the]] each gate electrode as a mask,

wherein a scanning direction of the energy beam changes outside and between the first element-forming region and the second element-forming region.

52. (Currently Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film by irradiating an energy beam output continuously while scanning the energy beam to a semiconductor film by moving the semiconductor film and the energy beam relatively;

forming a first element-forming region and a second element-forming region using portions of the crystalline semiconductor film;

forming a gate electrode in the first element-forming region and a gate electrode in the second element-forming region over ~~a portion of~~ the crystalline semiconductor film ~~which is included in an element forming region~~; and

forming an impurity region in the first element-forming region and an impurity region in the second element-forming region in the crystalline semiconductor film using [[the]] each gate electrode as a mask,

wherein the energy beam [[is]] starts or ends irradiation from outside the first element-forming region and the second element-forming region ~~or ends irradiation outside the element forming region~~ and changes a scanning direction between the first element-forming region and the second element-forming region.

53. (Currently Amended) A method for manufacturing ~~a thin film transistor~~ a semiconductor device according to claim 50, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

54. (Currently Amended) A method for manufacturing ~~a thin film transistor~~ a semiconductor device according to claim 50, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

55. (Previously Presented) A method for manufacturing a semiconductor device according to claim 50, wherein the semiconductor device is incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

56. (Previously Presented) A method for manufacturing a thin film transistor according to claim 51, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

57. (Previously Presented) A method for manufacturing a thin film transistor according to claim 51, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

58. (Currently Amended) A method for manufacturing a thin film transistor according to claim 51, wherein the first element-forming region is a region where a display device or an integrated circuit is formed and the second element-forming region is a region where a display device or an integrated circuit is formed.

59. (Currently Amended) A method for manufacturing a ~~semiconductor device~~ thin film transistor according to claim 51, wherein the ~~semiconductor device~~ thin film transistor is incorporated into a semiconductor device which is further incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

60. (Previously Presented) A method for manufacturing a thin film transistor according to claim 52, wherein the scanning of the energy beam is performed by using a galvanometer mirror or a polygon mirror.

61. (Previously Presented) A method for manufacturing a thin film transistor according to claim 52, wherein the energy beam output continuously is a beam emitted from a laser selected from the group consisting of a YVO_4 laser, a YAG laser, a YLF laser, a $YAlO_3$ laser, and an Ar laser.

62. (Currently Amended) A method for manufacturing a thin film transistor according to claim 52, wherein the first element-forming region is a region where a display device or an integrated circuit is formed and the second element-forming region is a region where a display device or an integrated circuit is formed.

63. (Currently Amended) A method for manufacturing a ~~semiconductor device~~ thin film transistor according to claim 52, wherein the ~~semiconductor device~~ thin film transistor is incorporated into a semiconductor device which is further incorporated into at least one selected from the group consisting of a display, a mobile computer, a game machine, and an electronic book reader.

64. (New) A method for manufacturing a thin film transistor according to claim 33, wherein the first element-forming region is a region where a display portion is formed and the second element-forming region is a region where a driver circuit is formed.

65. (New) A method for manufacturing a thin film transistor according to claim 34, wherein the first element-forming region is a region where a display portion is formed and the second element-forming region is a region where a driver circuit is formed.

66. (New) A method for manufacturing a thin film transistor according to claim 51, wherein the first element-forming region is a region where a display portion is

formed and the second element-forming region is a region where a driver circuit is formed.

67. (New) A method for manufacturing a thin film transistor according to claim 52, wherein the first element-forming region is a region where a display portion is formed and the second element-forming region is a region where a driver circuit is formed.